

ABSTRACT

The size of a power amplifier module as a semiconductor device is to be reduced. The power amplifier module comprises a module substrate having a main surface and a back surface, a lower chip flip-connected to the module substrate, an upper chip stacked face up onto the lower chip, a common electrode disposed on a back surface of the upper chip, plural wires for connecting the upper chip and the module substrate with each other, plural wires for connecting the common electrode and the module substrate with each other, plural chip parts mounted on the module substrate, and a sealing portion formed on the main surface of the module substrate. The common electrode is connected to the module substrate through wires to strengthen GND of the upper chip; besides, since the lower chip is flip-connected to the module substrate, the difference in size between the upper and lower chips is diminished to attain the reduction in size of the power amplifier module.